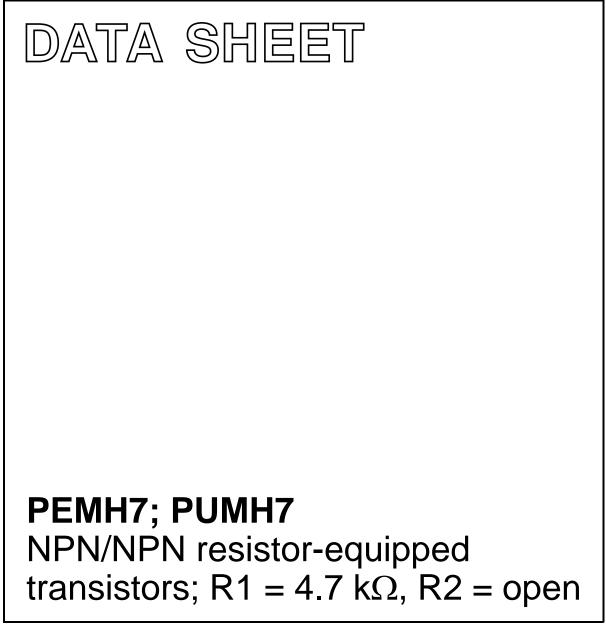
# **DISCRETE SEMICONDUCTORS**



Product data sheet Supersedes data of 2001 Oct 22 2003 Oct 02



# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

# PEMH7; PUMH7

MAX.

50

100

\_

UNIT

V

mΑ

\_

kΩ

TYP.

4.7

open

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

## APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

### DESCRIPTION

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

### **PRODUCT OVERVIEW**

TYPE NUMBER	PACKAGE			NPN/PNP	PNP/PNP	
ITPE NUMBER	PHILIPS			COMPLEMENT		
PEMH7	SOT666	-	H3	PEMD6	PEMB3	
PUMH7	SOT363	SC-88	H*7	PUMD6	PUMB3	

QUICK REFERENCE DATA

voltage

NPN

NPN

bias resistor

bias resistor

PARAMETER

output current (DC)

collector-emitter

SYMBOL

VCEO

 $I_{O}$ 

TR1

TR2

R1

R2

### Note

1. \* = p: Made in Hong Kong.

\* = t: Made in Malaysia.

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
ITPE NUMBER		PIN	DESCRIPTION	
PEMH7		1	emitter TR1	
PUMH7		2	base TR1	
		3	collector TR2	
		4	emitter TR2	
		5	base TR2	
		6	collector TR1	
	Top view MAM453			

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# PEMH7; PUMH7

### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE				
ITFE NOWBER	NAME	DESCRIPTION	VERSION		
PEMH7	MH7 – Plastic surface mounted package; 6 leads		SOT666		
PUMH7	PUMH7 – Plastic surface mounted package; 6 leads		SOT363		

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	or				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	-	300	mW
	SOT666	notes 1 and 2	-	300	mW

### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

# PEMH7; PUMH7

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
Per transist	tor				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	625	K/W	
	SOT666	notes 1 and 2	625	K/W	
Per device					
R <sub>th j-a</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$			
·	SOT363	note 1	416	K/W	
	SOT666	notes 1 and 2	416	K/W	

### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

## CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

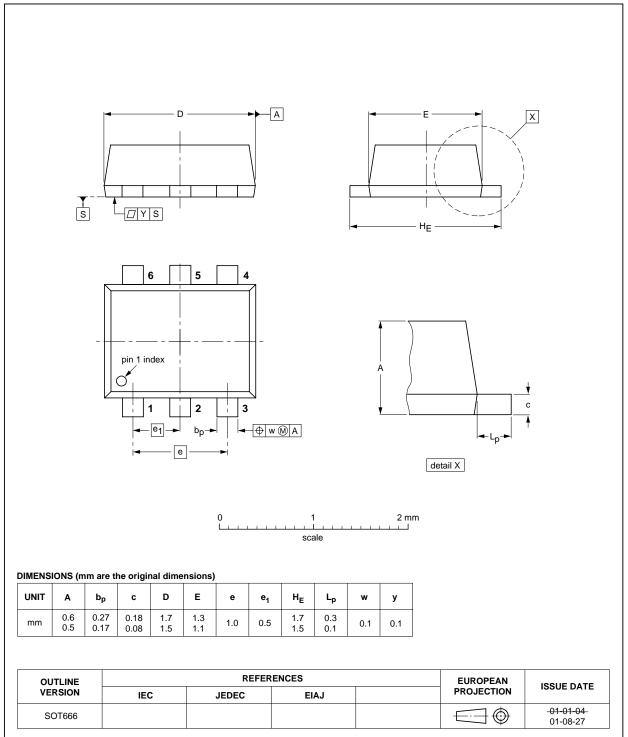
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Per transis	Per transistor						
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0$	-	-	100	nA	
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0$	-	-	1	μΑ	
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ	
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0$	-	-	100	nA	
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	330	-		
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	100	mV	
R1	input resistor		3.3	4.7	6.1	kΩ	
Cc	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	-	-	2.5	pF	

PEMH7; PUMH7

# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

### PACKAGE OUTLINE

## Plastic surface mounted package; 6 leads

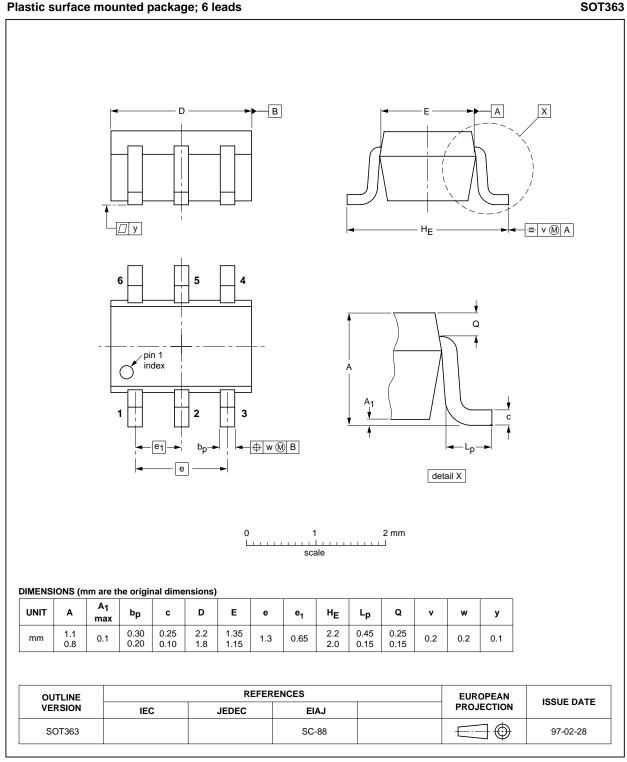


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SOT666

# NPN/NPN resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$ , R2 = open

# PEMH7; PUMH7



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SOT363

# NPN/NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = open

# PEMH7; PUMH7

### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

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# **NXP Semiconductors**

### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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